

BCW89
SURFACE MOUNT
PNP SILICON TRANSISTOR



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BCW89 is a Silicon PNP Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose applications.

MARKING CODE: H3

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Emitter Voltage	V_{CEO}	60	V
Collector-Base Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C}/\text{W}$

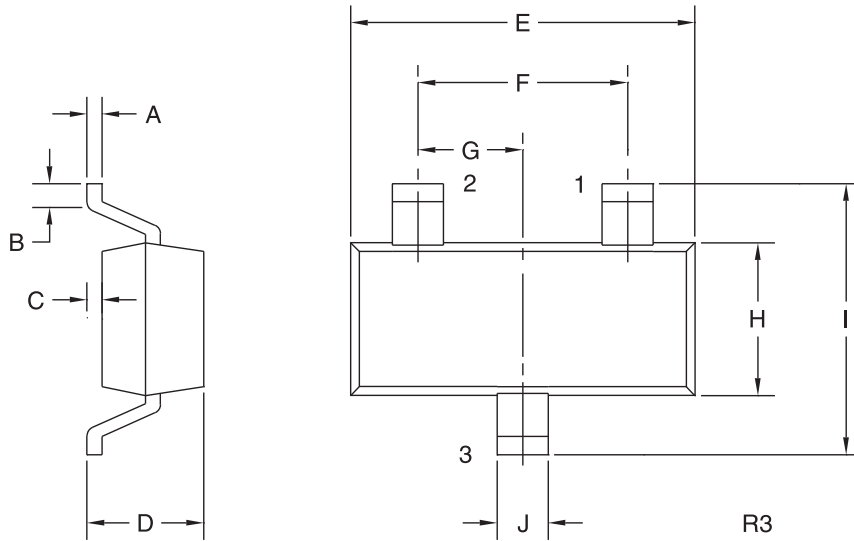
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		100	nA
I_{CBO}	$V_{CB}=20\text{V}, T_A=100^\circ\text{C}$		10	μA
BV_{CBO}	$I_C=10\mu\text{A}$	80		V
BV_{CEO}	$I_C=2.0\text{mA}$	60		V
BV_{CES}	$I_C=10\mu\text{A}$	60		V
BV_{EBO}	$I_C=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		300	mV
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	600	750	mV
h_{FE}	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	120	260	
NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=2.0\text{k}\Omega$ $f=1.0\text{kHz}, B=200\text{Hz}$		10	dB

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:
 1) BASE
 2) EMITTER
 3) COLLECTOR

MARKING CODE: H3

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (20-November 2009)